

东莞市华远电子有限公司

DONG GUAN SHI HUA YUAN ELECTRON CO..LTD.

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TO-92 Plastic-Encapsulate Transistors

2SA836 TRANSISTOR (PNP)

FEATURES

Power dissipation

 P_{CM} : 0.2 W (Tamb=25)

Collector current

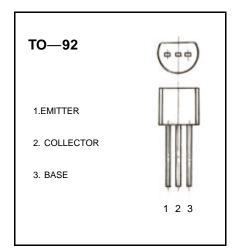
I_{CM}: -0.1 A

Collector-base voltage

 $V_{(BR)CBO}$: -55 V

Operating and storage junction temperature range

 T_J , T_{stg} : -55 to +150

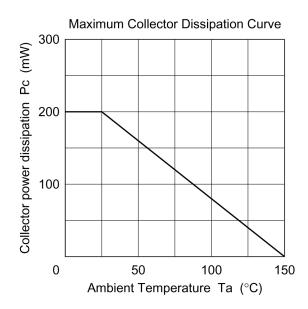


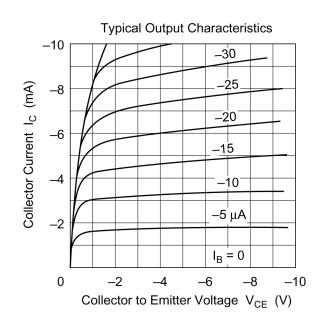
ELECTRICAL CHARACTERISTICS (Tamb=25 unless otherwise specified)

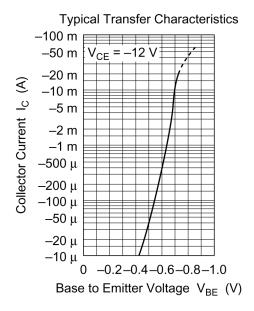
Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V _{(BR)CBO}	Ic= -10 μ A , I _E =0	-55			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I_{C} = -1 mA , I_{B} =0	-55			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = -10 μ A , I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-18V, I _E =0			-0.1	μА
Emitter cut-off current	I _{EBO}	V _{EB} = -2V , I _C =0			-0.05	μА
DC current gain	h _{FE}	V _{CE} =-12 V, I _C = -2mA	160		500	
Collector-emitter saturation voltage	V _{CEsat}	I _C = -10mA, I _B = -1mA			-0.5	V
Base-emitter voltage	V _{BE} (ON)	V _{CE} =-12 V, I _C = -2mA			-0.75	V
Transition frequency	f _T	V _{CE} =-12 V, I _C = -2mA	150			MHz
Output capacitance	C _{ob}	V _{CE} =-10V, I _E =0,f=1 MHz			4	pF
Noise figure	NF	V_{CE} =-6V , I_{C} =0.1 mA , I_{C} =1 0Hz , I_{C} =10K			5	dB
Troise light		V_{CE} =-6V , I_{C} =0.1 mA , f=1 kHz , R_{G} =10K			1	

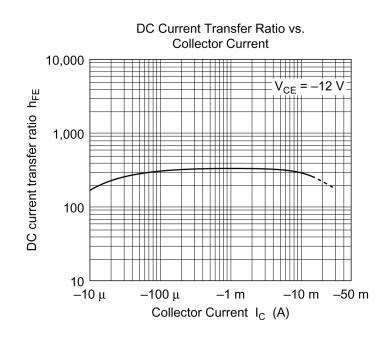
CLASSIFICATION OF hFE

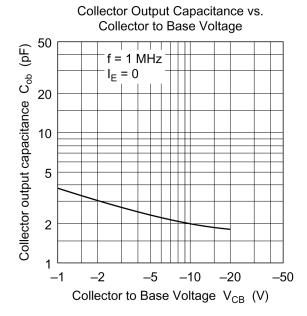
Rank C		D		
Range	160-320	250-500		

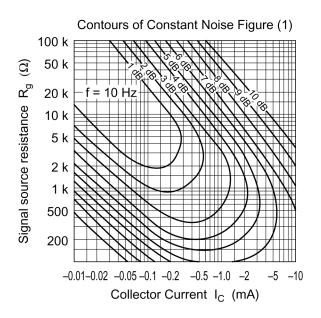


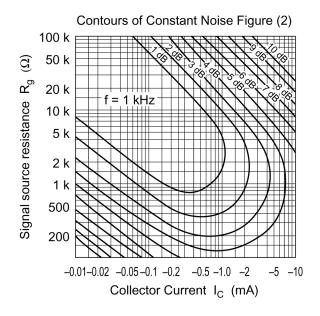












TO-92 PACKAGE OUTLINE DIMENSIONS





Symbol	Dimensions I	n Millimeters	Dimensions In Inches		
	Min	Max	Min	Max	
Α	3.300	3.700	0.130	0.146	
A1	1.100	1.400	0.043	0.055	
b	0.380	0.550	0.015	0.022	
С	0.360	0.510	0.014	0.020	
D	4.400	4.700	0.173	0.185	
D1	3.430		0.135		
E	4.300	4.700	0.169	0.185	
е	1.270TYP		0.050TYP		
e1	2.440	2.640	0.096	0.104	
L	14.100	14.500	0.555	0.571	
Ö		1.600		0.063	
$\overline{}$	0.000	0.380	0.000	0.015	